

**PROBLEM SET #4**

Issued: Tuesday, Feb.14, 2012

Due: Tuesday, Feb.21, 2012, 6:00 p.m. in the EE 140 homework box in 240 Cory

1. (a) For the two BJT current mirror circuits shown in Fig. PS4.11, calculate the ideal mirror ratio  $I_O/I_{REF}$  if (i)  $V_A = \infty$  and  $\beta_{FO} = \infty$ . (ii) If  $V_A = \infty$  and  $\beta_{FO} = 75$ . (iii) If  $V_A = 60$  V,  $\beta_{FO} = 75$ , and  $V_{BE} = 0.7$  V. The symbol “A” stands for the relative sizes of the emitters of the BJT.

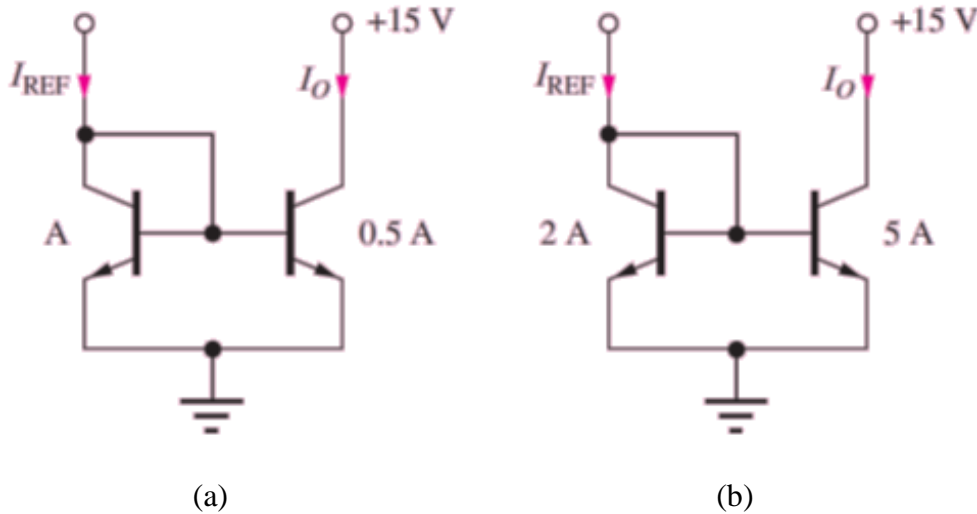


Fig. PS4.11

- (b) Calculate the mirror ratio  $I_O/I_{REF}$  for the MOS current mirrors in the Fig PS4.12 for (i)  $\lambda=0$ ; (ii) For  $\lambda = 0.02$  V<sup>-1</sup> if  $V_{TN} = 1$  V,  $k' = 25$   $\mu$ A/V<sup>2</sup>, and  $I_{REF} = 50$   $\mu$ A.

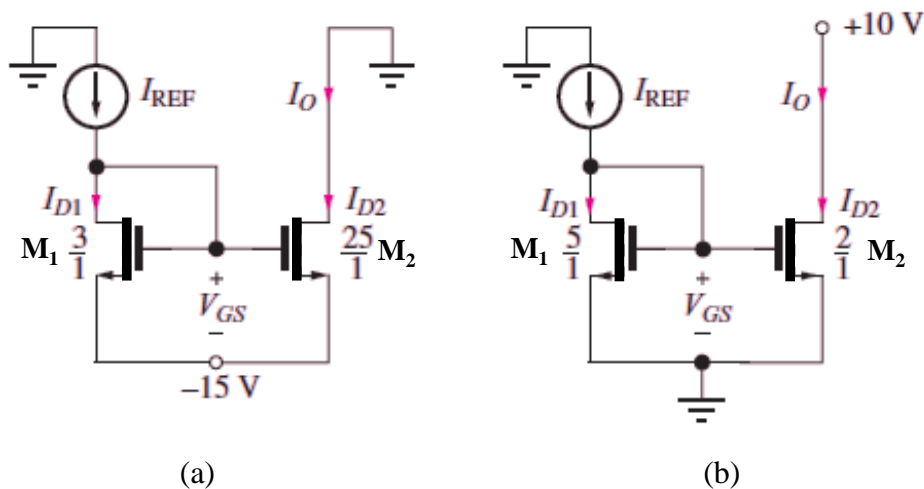


Fig PS4.12

(c) If a small ac voltage disturbance  $v_n$  is applied directly at the  $M_1$  gate as shown below in Fig PS4.13, what is the output current disturbance  $i_n$  due to  $v_n$  for (i)  $\lambda=0$ ; (ii)  $\lambda = 0.02 \text{ V}^{-1}$  if  $V_{TN} = 1 \text{ V}$ ,  $k = 25 \mu\text{A/V}^2$ , and  $I_{REF} = 50 \mu\text{A}$ .

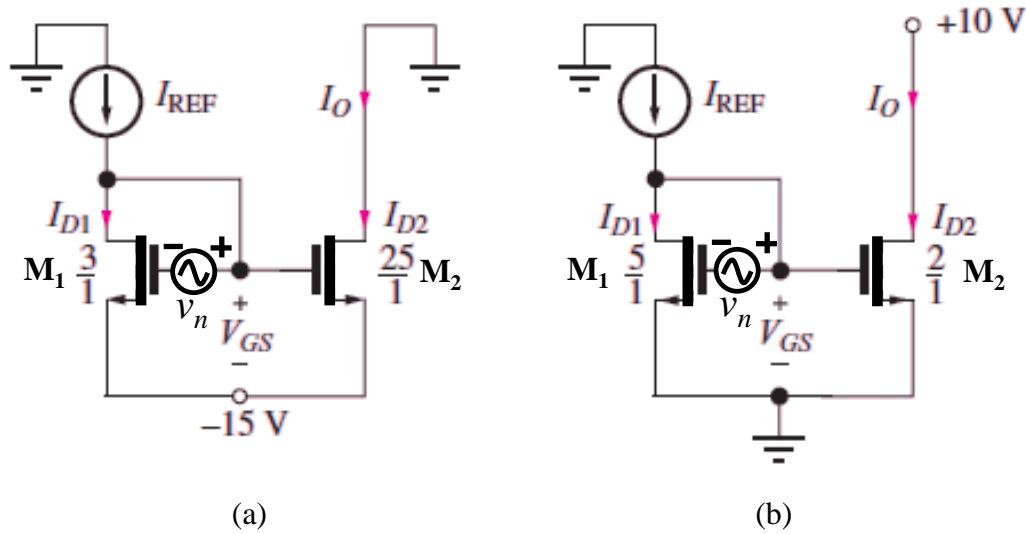


Fig. PS4.13

- Calculate the gain of each circuit in Fig. PS4.2 at very low and very high frequencies. Neglect all other capacitances and assume  $\lambda=\gamma=0$ .

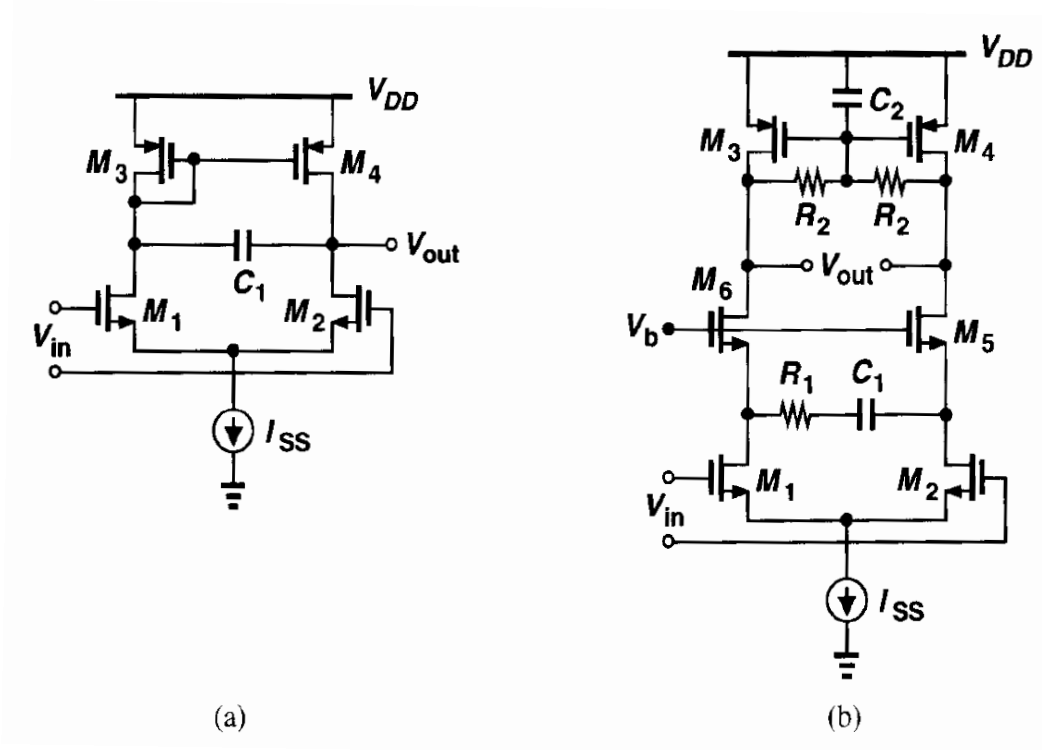


Fig. PS4.2

3. For the BJT Wildar current source shown in Fig. PS4.3, assume  $V_{CC} = 5V$ ,  $R_1 = 4.3k\Omega$ ,  $V_{BE(on)} = 0.7V$ .
- Determine the proper value of  $R_2$  to give  $I_{out} = 5mA$ , assume  $\beta_F = 100$
  - What is the output resistance of the current source, assume  $V_A = 80V$ ,  $\beta_F = 100$ .
  - Determine the sensitivity of  $I_{out}$  to the power-supply voltage  $S_{V_{CC}}^{I_{OUT}}$ . ( $S_{V_{CC}}^{I_{OUT}} = \frac{V_{CC}}{I_{OUT}} \frac{\partial I_{OUT}}{\partial V_{CC}}$ )

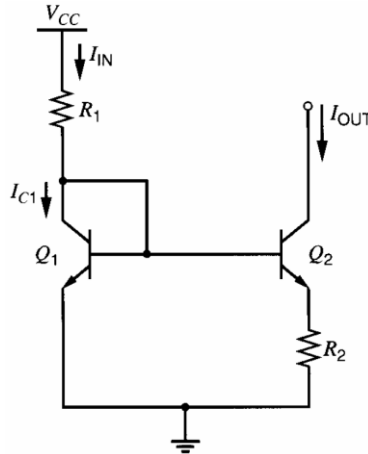


Fig. PS4.3

4. Calculate the mid-band small-signal gain and -3dB frequency of the circuit in Fig. PS4.4. Assume:  $R_S = 1\text{ k}\Omega$ ,  $R_E = 75\ \Omega$ ,  $R_3 = 4\text{ k}\Omega$ ,  $R_L = 1\text{ k}\Omega$ ,  $R_1 = 4\text{ k}\Omega$ ,  $R_2 = 10\text{ k}\Omega$ , and  $V_{CC} = V_{EE} = 10V$ . Device data are  $\beta = 200$ ,  $V_{BE(on)} = 0.7\text{ V}$ ,  $\tau_F = 0.25\text{ ns}$ ,  $r_b = 200\ \Omega$ ,  $r_c$  (active region)  $= 150\ \Omega$ ,  $C_{je0} = 1.3\text{ pF}$ ,  $C_{\mu0} = 0.6\text{ pF}$ ,  $\psi_{oc} = 0.6\text{ V}$ ,  $C_{cs0} = 2\text{ pF}$ ,  $\psi_{os} = 0.58\text{ V}$ , and  $n_s = 0.5$ . Also you can assume  $C_{je}$  in forward active region equals  $2C_{je0}$ .

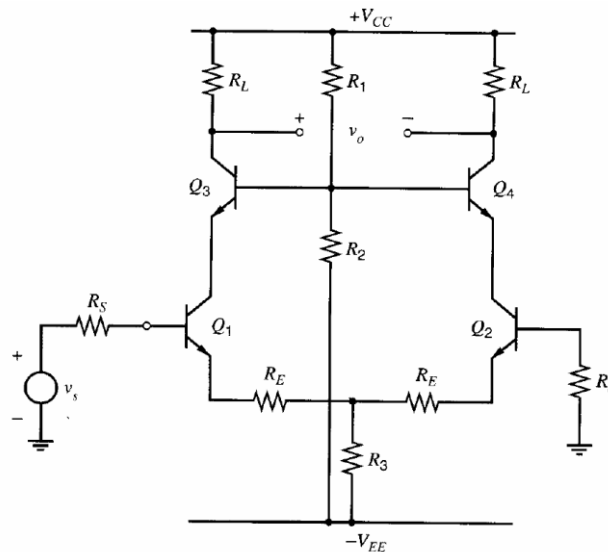


Fig. PS4.4